



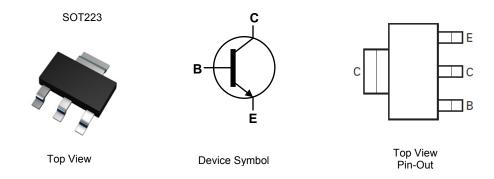
60V NPN LOW SATURATION TRANSISTOR IN SOT223

Features

- BV_{CEO} > 60V
- I_C = 6A High Continuous Current
- I_{CM} = 12A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < 60mV @ 1A
- Complementary PNP Type: DSS60600MZ4
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case material: molded plastic. "Green" molding compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 63
- Weight: 0.115 grams (approximate)



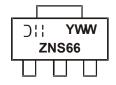
Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape width (mm)	Quantity per reel
DSS60601MZ4-13	AEC-Q101	ZNS66	13	12	2500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



ZNS66 = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year (ex: 4 = 2014) WW = Week code 01 - 52



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	100	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	6	V
Continuous Collector Current	Ic	6	Α
Peak Pulse Collector Current	I _{CM}	12	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
	(Note 5)		3	
Power Dissipation	(Note 6)	P _D	2	W
	(Note 7)		1.2	
	(Note 5)	41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ heta JA}$	62.5	°C/W
	(Note 7)		104	
Thermal Resistance, Junction to Leads (Note 8	R ₀ JL	12.9	°C/W	
Operating and Storage Temperature Range	T _{J.} T _{STG}	-55 to +150	°C	

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

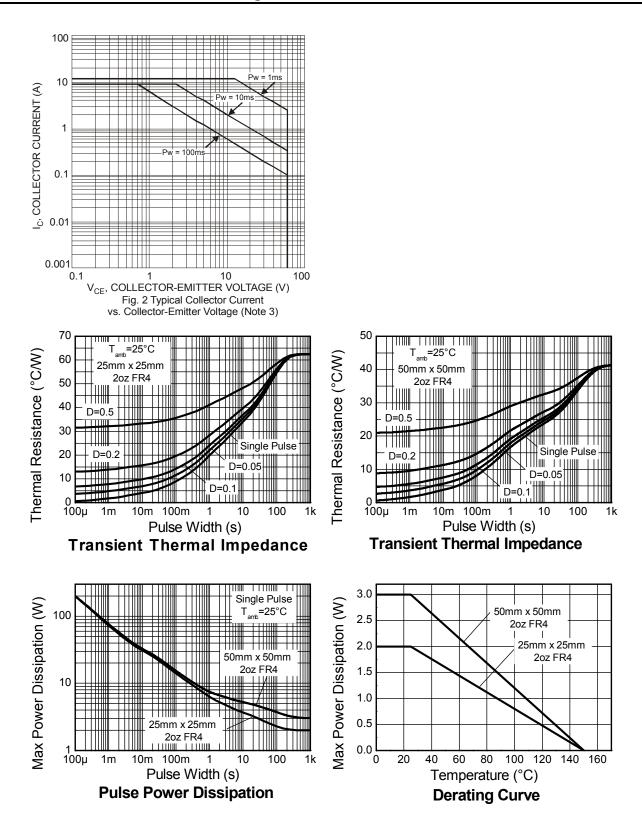
- 5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
- 6. Same as note (5), except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as note (5), except the device is mounted on minimum recommended pad (MRP) layout.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead). 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

March 2014

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Thermal Characteristics and Derating Information





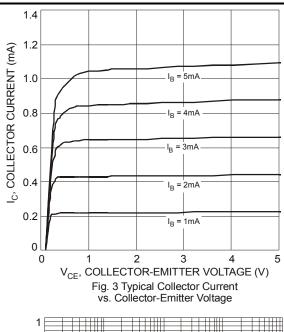
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

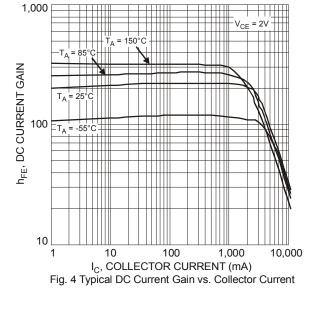
Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS				<u>.</u>		
Collector-Base Breakdown Voltage	BV _{CBO}	100	_	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	60	_	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	6	_	_	V	I _E = 100μA
Collector-Base Cutoff Current	1		_	100	nA	$V_{CB} = 40V, I_{E} = 0$
Collector-base Cuton Current	Ісво		_	50	μΑ	$V_{CB} = 40V$, $I_E = 0$, $T_J = 150$ °C
Emitter-Base Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 6V, I_{C} = 0$
ON CHARACTERISTICS (Note 10)						
		150	_	_		$V_{CE} = 2V, I_{C} = 0.5A$
DC Current Gain	hee	120	_	360		$V_{CE} = 2V$, $I_C = 1A$
DC Current Gain	h _{FE}	100	_	_	_	$V_{CE} = 2V$, $I_C = 2A$
		50		_		$V_{CE} = 2V$, $I_C = 6A$
			_	40		$I_C = 0.1A$, $I_B = 2.0mA$
		_	_	60	mV	I _C = 1A, I _B = 100mA
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		80	100		I _C = 2A, I _B = 200mA
			_	220		I _C = 3A, I _B = 60mA
			_	300		I _C = 6A, I _B = 600mA
Equivalent On-Resistance	R _{CE(SAT)}		40	50	$m\Omega$	I _E = 2A, I _B = 200mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$		_	0.9	V	I _C = 1A, I _B = 100mA
Base-Emitter Turn-on Voltage	V _{BE(ON)}		_	0.9	V	$V_{CE} = 2V$, $I_C = 1A$
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	100	_	_	MHz	V _{CE} = 10V, I _C = 100mA, f = 100MHz
Output Capacitance	C _{obo}		26	_	pF	V _{CB} = 10V, f = 1MHz
Input Capacitance	C _{ibo}		325	_	pF	V _{EB} = 5V, f = 1MHz
Turn-On Time	t _{on}	1	87	_	ns	
Delay Time	t _d	_	41	_	ns] _V = 20.
Rise Time	t _r		46	_	ns	$V_{CC} = -30v$,
Turn-Off Time	t _{off}	1	294	_	ns	I _{CC} = 150mA I _{B1} = - I _{B2} =15mA
Storage Time	ts		250	_	ns	181 182 - IOINA
Fall Time	t _f	_	44	_	ns	

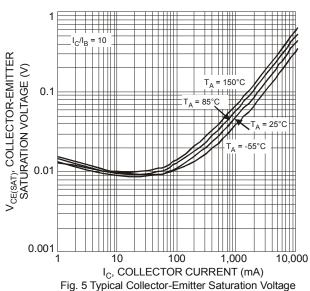
Notes: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



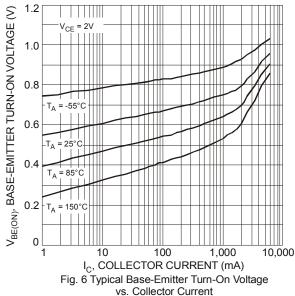
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)







vs. Collector Current





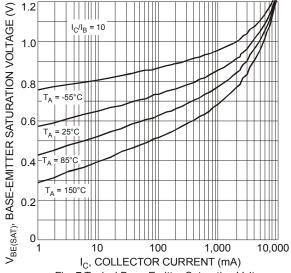


Fig. 7 Typical Base-Emitter Saturation Voltage vs. Collector Current

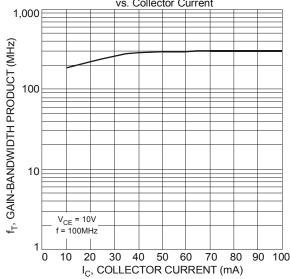


Fig. 9 Typical Gain-Bandwidth Product vs. Collector Current

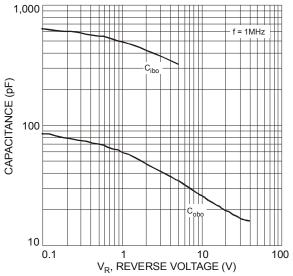
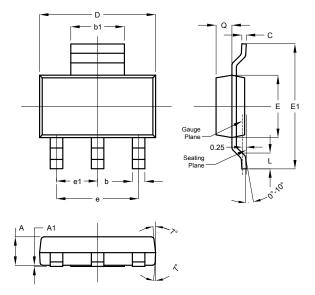


Fig. 8 Typical Capacitance Characteristics



Package Outline Dimensions

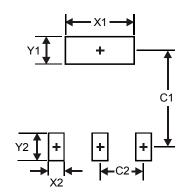
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
E	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All [All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X1	3.3
X2	1.2
Y1	1.6
Y2	1.6
C1	6.4
C2	2.3



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